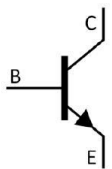


Silicon NPN transistor in a TO-92 Plastic Package.

High frequency.

High frequency amplifier.

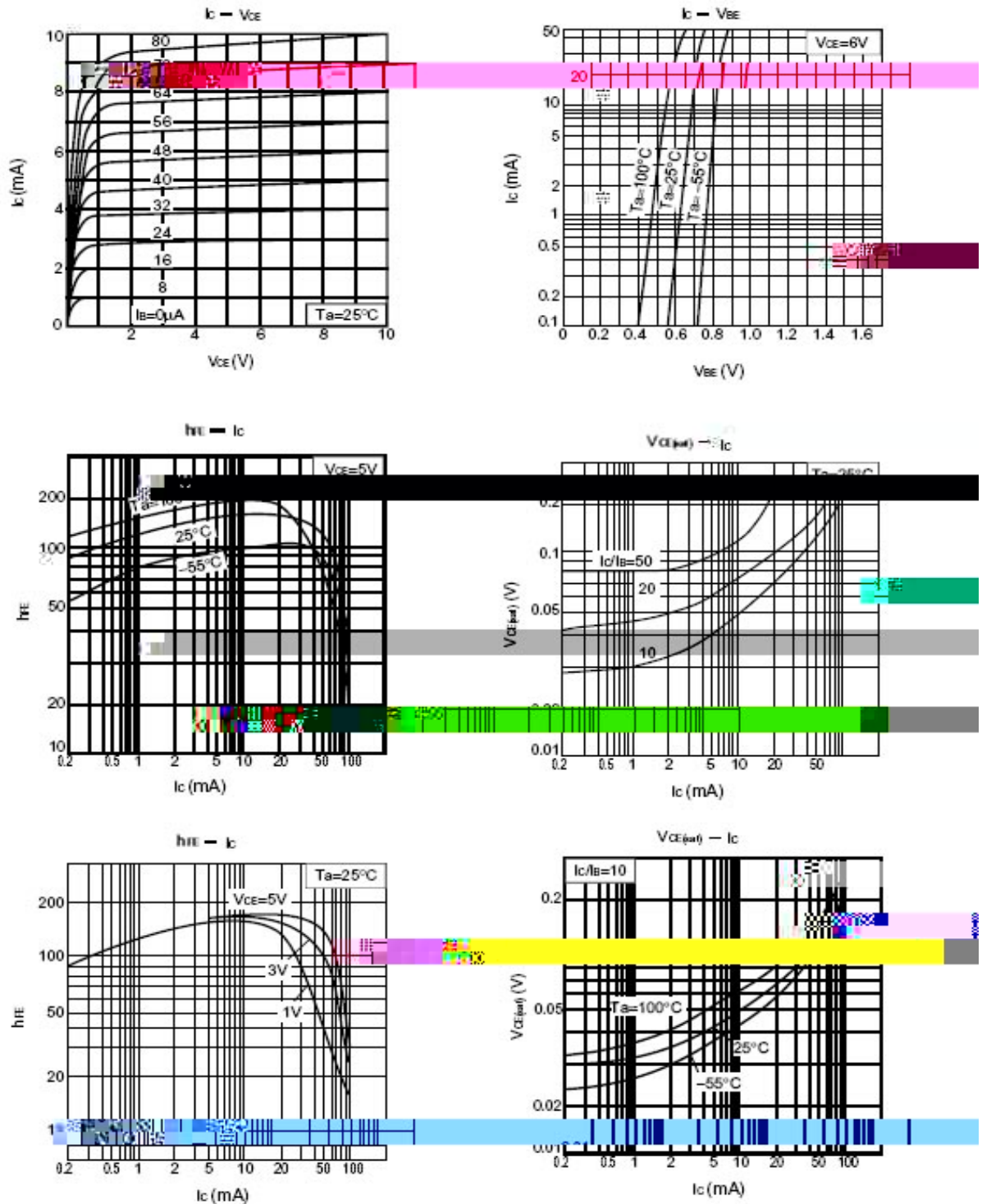


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	P
h_{FE} Range	82~180

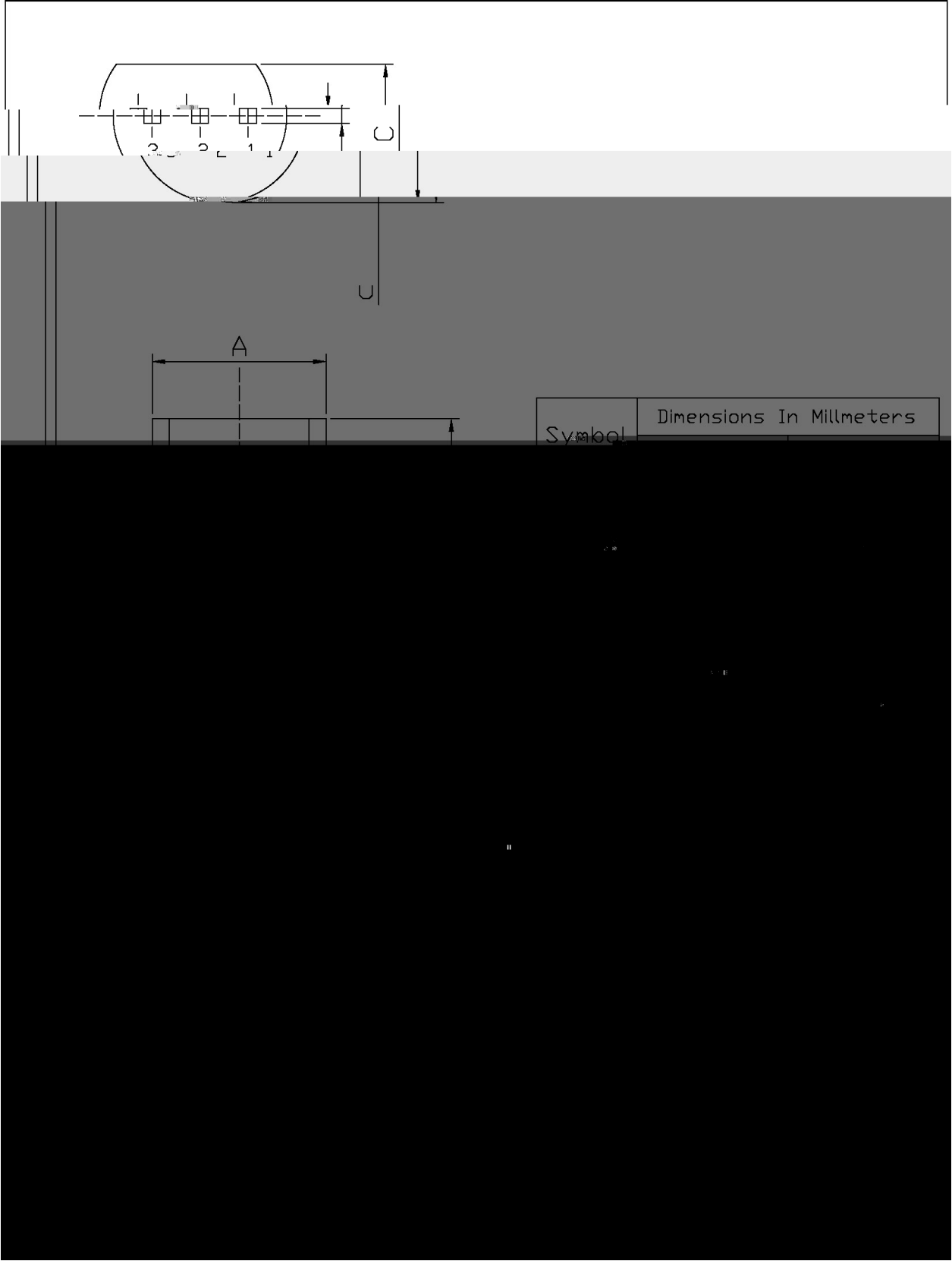
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\text{ A}$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0\text{mA}$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\text{ A}$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=24\text{V}$ $I_E=0$			0.5	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=3.0\text{V}$ $I_C=0$			0.5	A
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10\text{mA}$ $I_B=1.0\text{mA}$		0.1	0.3	V
DC Current Gain	h_{FE}	$V_{CE}=6.0\text{V}$ $I_C=1.0\text{mA}$	82		180	
Transition Frequency	f_T	$V_{CE}=6.0\text{V}$ $f=100\text{MHz}$ $I_E=-1.0\text{mA}$	150	300		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0\text{V}$ $f=1.0\text{MHz}$ $I_E=0$		1.3	2.2	pF

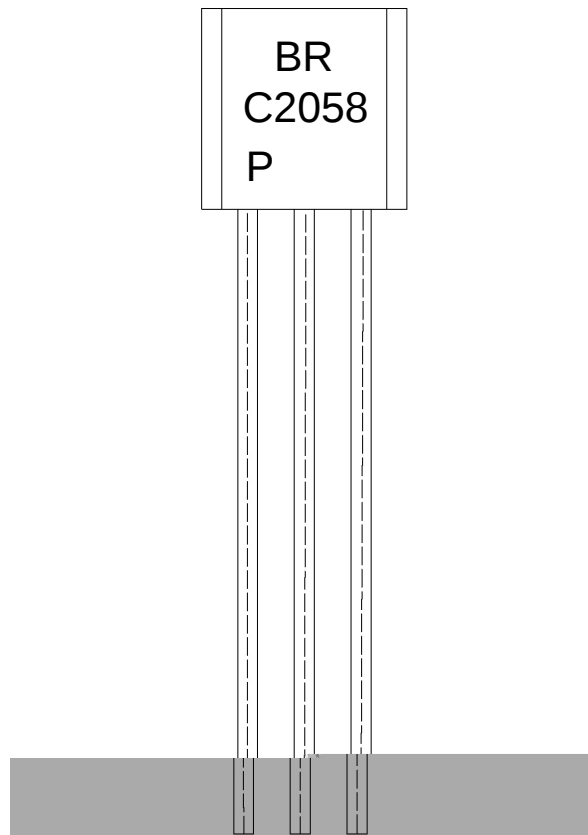


T0-92

Unit: mm



Symbol	Dimensions In Millimeters
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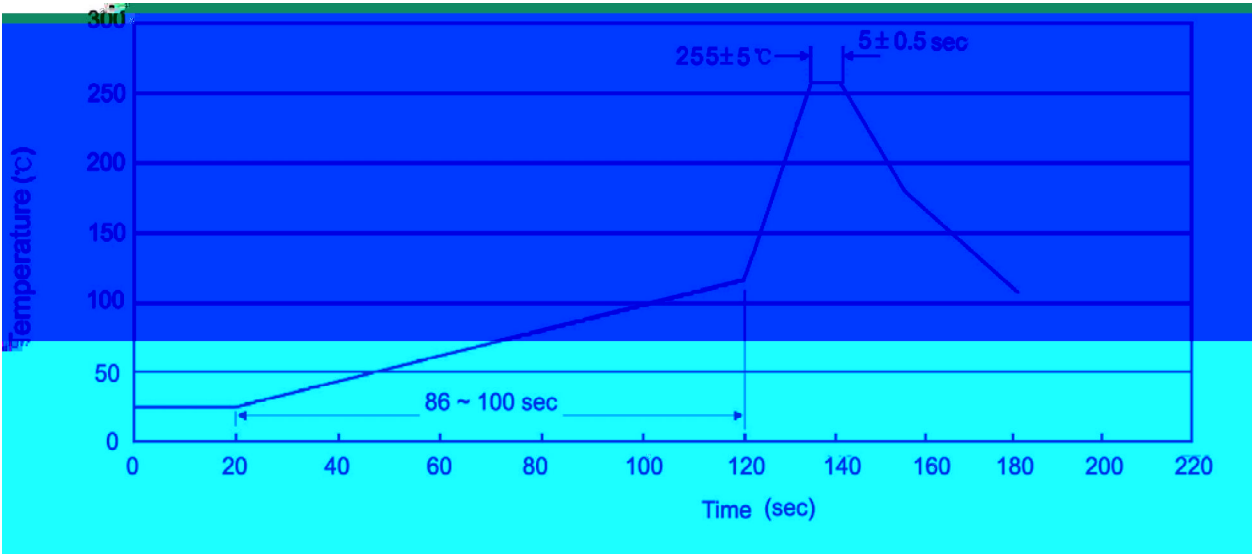
Note:

BR: Company Code.

C2058: Product Type.

P: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

，Time:60~90sec.
- 2.Peak Temp.:255 5

，Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 大箱